

AMENDMENTS

In the Specification

Please replace the title with:

--Circuitry and Gate Stacks Encompassing a Semiconductive Substrate, A Metal Silicide Layer And An Inorganic Material Layer In Physical Contact With The Metal Silicide Layer--.

Please replace the Abstract of Disclosure with the following clean replacement paragraph in accordance with 37 C.F.R. §1.121(b)(1)(ii):

B1 The present invention includes semiconductor circuitry. Such circuitry encompasses a metal silicide layer over a substrate and a layer comprising silicon, nitrogen and oxygen in physical contact with the metal silicide layer. The present invention also includes a gate stack which encompasses a polysilicon layer over a substrate, a metal silicide layer over the polysilicon layer, an antireflective material layer over the metal silicide layer, a silicon nitride layer over the antireflective material layer, and a layer of photoresist over the silicon nitride layer, for photolithographically patterning the layer of photoresist to form a patterned masking layer from the layer of photoresist and transferring a pattern from the patterned masking layer to the silicon nitride layer, antireflective material layer, metal silicide layer and polysilicon layer. The patterned silicon nitride layer, antireflective material layer, metal silicide layer and polysilicon layer encompass a gate stack.